

ZXTP25012EZ

20V PNP high gain transistor in SOT89

Summary

$BV_{CEO} > -12V$

$h_{FE} > 500$

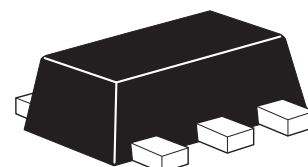
$I_{C(cont)} = 4.5A$

$V_{CE(sat)} < -70mV @ 1A$

$R_{CE(sat)} = 45m\Omega$

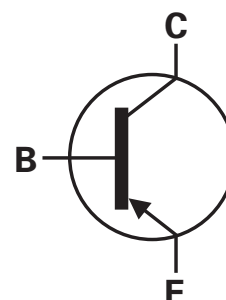
$P_D = 2.4W$

Complementary part number ZXTN25012EZ



Description

Packaged in the SOT89 outline this new low saturation 12V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

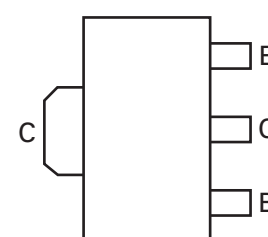


Features

- 4.5A continuous current
- Up to 10A peak current
- Very low saturation voltages
- High gain

Applications

- High side switch
- Battery charging
- Regulator circuits
- Buck converters
- MOSFET gate drivers



Pinout - top view

Ordering information

| Device | Reel size (inches) | Tape width (mm) | Quantity per reel |
|---------------|--------------------|-----------------|-------------------|
| ZXTP25012EZTA | 7 | 12 | 1000 |

Device marking

- 1L4

ZXTP25012EZ

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|---|----------------|------------|-------|
| Collector-Base voltage | V_{CBO} | -20 | V |
| Collector-Emitter voltage | V_{CEO} | -12 | V |
| Emitter-Base voltage | V_{EBO} | -7 | V |
| Continuous Collector current ^(c) | I_C | -4.5 | A |
| Base current | I_B | -1 | A |
| Peak pulse current | I_{CM} | -10 | A |
| Power dissipation at $T_A = 25^\circ\text{C}^{(a)}$ | P_D | 1.1 | W |
| Linear derating factor | | 8.8 | mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}^{(b)}$ | P_D | 1.8 | W |
| Linear derating factor | | 14.4 | mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}^{(c)}$ | P_D | 2.4 | W |
| Linear derating factor | | 19.2 | mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}^{(d)}$ | P_D | 4.46 | W |
| Linear derating factor | | 35.7 | mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}^{(d)}$ | P_D | 19.2 | W |
| Linear derating factor | | 153 | mW/°C |
| Operating and storage temperature range | T_j, T_{stg} | -55 to 150 | °C |

Thermal resistance

| Parameter | Symbol | Limit | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\theta JA}$ | 117 | °C/W |
| Junction to ambient ^(b) | $R_{\theta JA}$ | 68 | °C/W |
| Junction to ambient ^(c) | $R_{\theta JA}$ | 51 | °C/W |
| Junction to ambient ^(d) | $R_{\theta JA}$ | 28 | °C/W |
| Junction to case ^(e) | $R_{\theta JC}$ | 7.95 | °C/W |

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

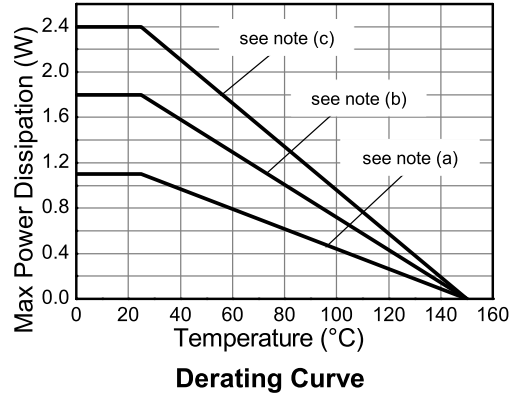
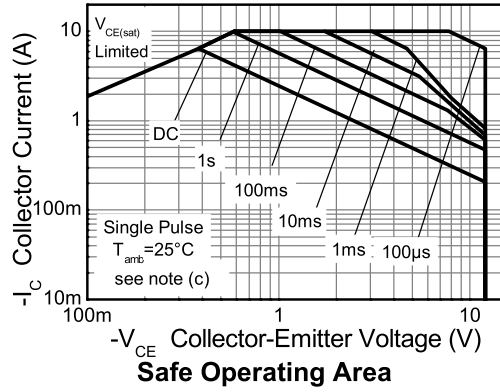
(c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(d) As (c) above measured at $t < 5$ seconds.

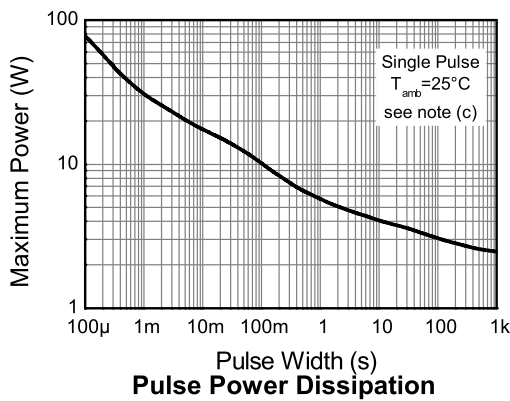
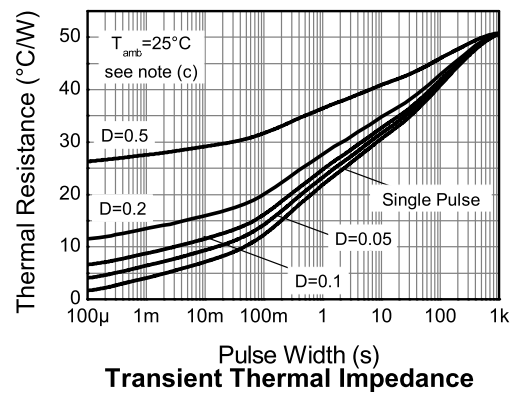
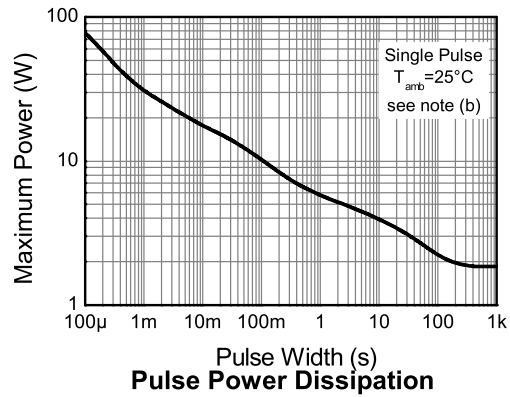
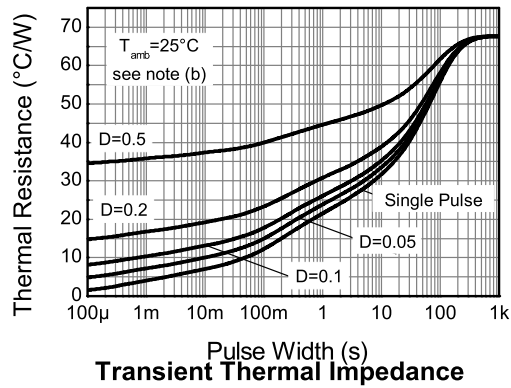
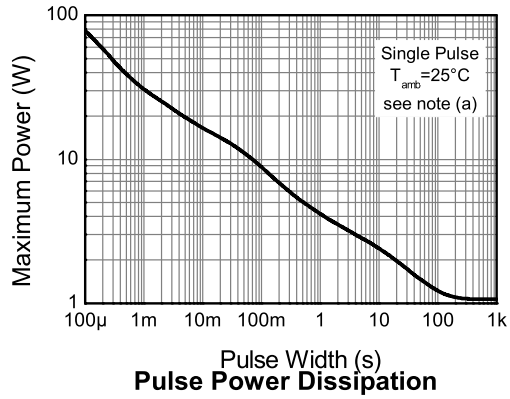
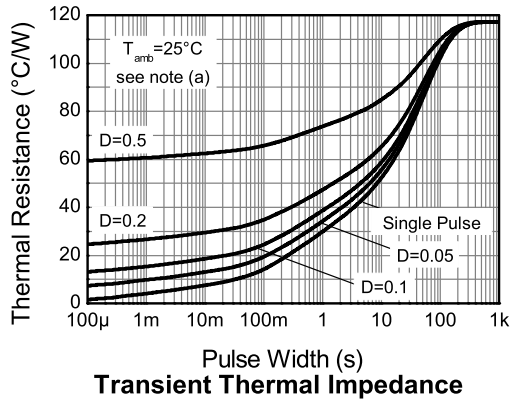
(e) Junction to case (collector tab). Typical

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Thermal characteristics



Thermal characteristics



ZXTP25012EZ

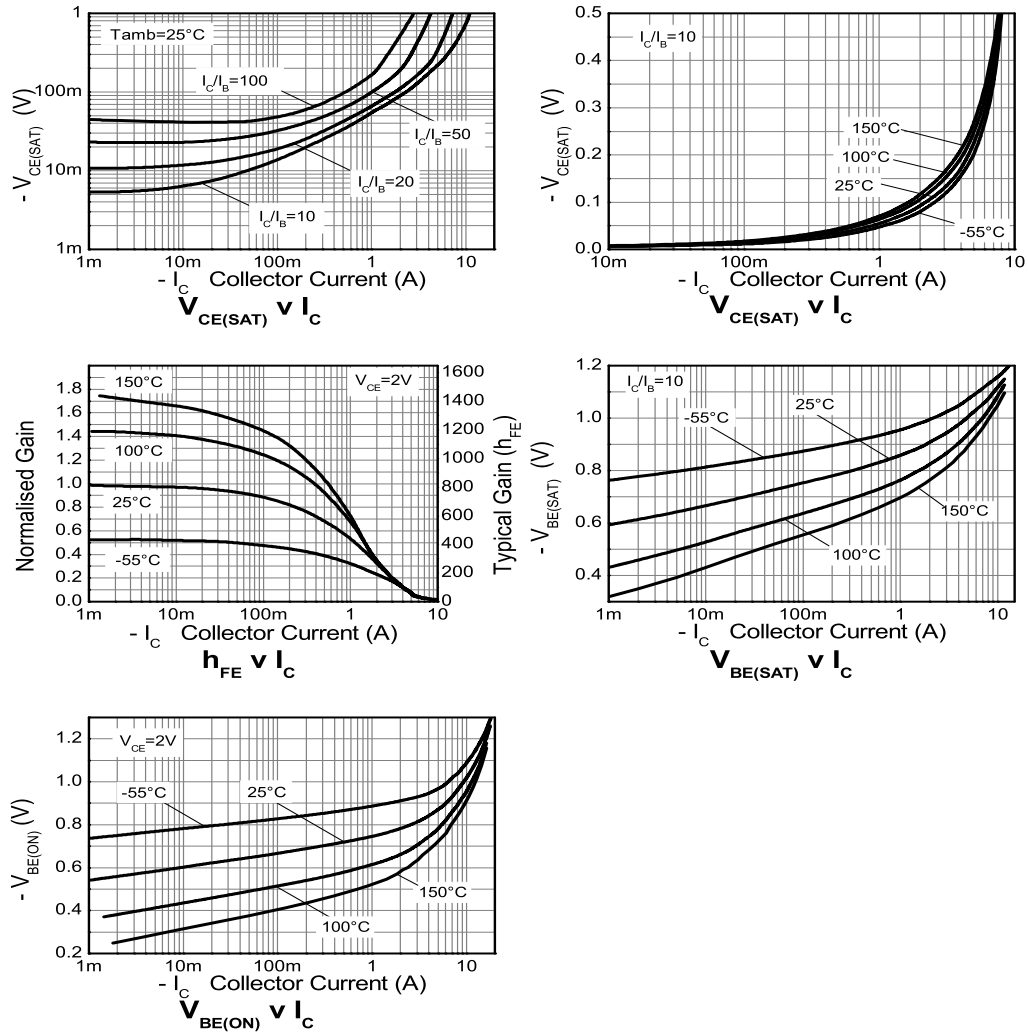
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---------------------------------------|---------------|------------------|-----------------------------|-----------------------------|----------------------|---|
| Collector-Base breakdown voltage | BV_{CBO} | -12 | -35 | | V | $I_C = -100\mu\text{A}$ |
| Collector-Emitter breakdown voltage | BV_{CEO} | -12 | -25 | | V | $I_C = -10\text{mA}^{(*)}$ |
| Emitter-Base breakdown voltage | BV_{EBO} | -7 | -8.5 | | V | $I_E = -100\mu\text{A}$ |
| Collector-Base cut-off current | I_{CBO} | | <-1 | -50 -0.5 | nA μA | $V_{CB} = -12\text{V}$ $V_{CB} = -12\text{V}, T_{amb}=100^{\circ}\text{C}$ |
| Emitter Base cut-off current | I_{EBO} | | <-1 | -50 | nA | $V_{EB} = -5.6\text{V}$ |
| Collector-Emitter saturation voltage | $V_{CE(sat)}$ | | -55 -155 -185 -200 | -70 -265 -355 -285 | mV mV mV mV | $I_C = -1\text{A}, I_B = -100\text{mA}^{(*)}$ $I_C = -1\text{A}, I_B = -10\text{mA}^{(*)}$ $I_C = -2\text{A}, I_B = -40\text{mA}^{(*)}$ $I_C = -4.5\text{A}, I_B = -450\text{mA}^{(*)}$ |
| Base-Emitter saturation voltage | $V_{BE(sat)}$ | | -990 | -1100 | mV | $I_C = -4.5\text{A}, I_B = -450\text{mA}^{(*)}$ |
| Base-Emitter turn-on voltage | $V_{BE(on)}$ | | -865 | -975 | mV | $I_C = -4.5\text{A}, V_{CE} = -2\text{V}^{(*)}$ |
| Static forward current transfer ratio | h_{FE} | 500 300 40 | 800 450 85 15 | 1500 | | $I_C = -10\text{mA}, V_{CE} = -2\text{V}^{(*)}$ $I_C = -1\text{A}, V_{CE} = -2\text{V}^{(*)}$ $I_C = -4.5\text{A}, V_{CE} = -2\text{V}^{(*)}$ $I_C = -10\text{A}, V_{CE} = -2\text{V}^{(*)}$ |
| Transition frequency | f_T | | 310 | | MHz | $I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$ |
| Input capacitance | C_{ibo} | | 127 | 250 | pF | $V_{EB} = -0.5\text{V}, f = 1\text{MHz}^{(*)}$ |
| Output capacitance | C_{obo} | | 16.9 | 30 | pF | $V_{CB} = -10\text{V}, f = 1\text{MHz}^{(*)}$ |
| Delay time | t_d | | 41 | | ns | $V_{CC} = -10\text{V}, I_C = -1\text{A},$ $I_{B1} = -I_{B2} = -10\text{mA}$ |
| Rise time | t_r | | 62 | | ns | |
| Storage time | t_s | | 179 | | ns | |
| Fall time | t_f | | 65 | | ns | |

NOTES:

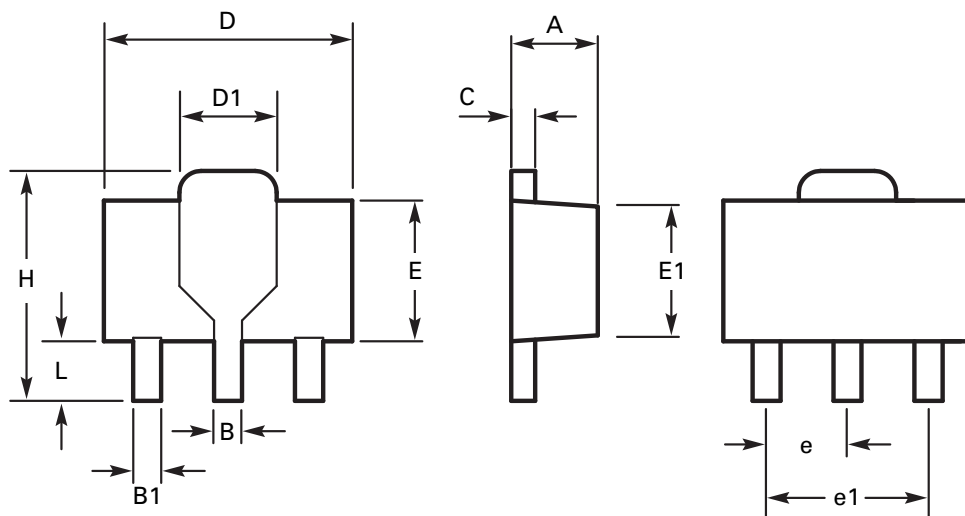
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTP25012EZ

Package outline



| DIM | Millimeters | | Inches | | DIM | Millimeters | | Inches | |
|-----|-------------|------|--------|-------|-----|-------------|------|-----------|-------|
| | Min | Max | Min | Max | | Min | Max | Min | Max |
| A | 1.40 | 1.60 | 0.550 | 0.630 | E | 2.29 | 2.60 | 0.090 | 0.102 |
| B | 0.44 | 0.56 | 0.017 | 0.022 | E1 | 2.13 | 2.29 | 0.084 | 0.090 |
| B1 | 0.36 | 0.48 | 0.014 | 0.019 | e | 1.50 BSC | | 0.059 BSC | |
| C | 0.35 | 0.44 | 0.014 | 0.017 | e1 | 3.00 BSC | | 0.118 BSC | |
| D | 4.40 | 4.60 | 0.173 | 0.181 | H | 3.94 | 4.25 | 0.155 | 0.167 |
| D1 | 1.52 | 1.83 | 0.064 | 0.072 | L | 0.89 | 1.20 | 0.035 | 0.047 |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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| | |
|-----------------------|---|
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